

Description

The PSJMTO60R1000 is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

MOSFET Product Summary

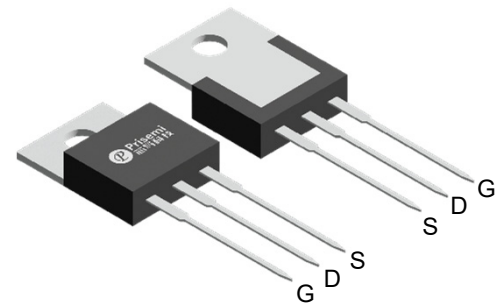
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
600	785 @ $V_{GS} = 10V$	3.3

Feature

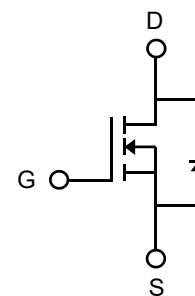
- Fast Switching Capability
- Lead free product is acquired.
- Avalanche Energy Tested

Applications

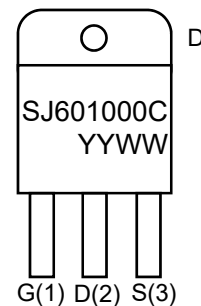
- PWM applications
- Load Switch
- Power Management
- DC-DC Converters



**TO-220
Bottom View**



Circuit Diagram



Marking (Top View)

Absolute maximum rating@25°C

Rating		Symbol	Value	Units
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	±30	V
Drain Current-Continuous ¹⁾	$T_C=25^\circ C$	I_D	3.3	A
	$T_C=100^\circ C$		2.1	
Pulsed Drain Current ²⁾		I_{DM}	7.0	A
Total Power Dissipation ³⁾		P_D	54.3	W
Avalanche Current ⁴⁾		I_{AS}	1.5	A
Avalanche Energy ⁴⁾		E_{AS}	21.5	mJ
Thermal Resistance , Junction-to-Case ⁵⁾		$R_{\theta JC}$	2.3	°C/W
Thermal Resistance , Junction-to-Ambient ⁶⁾		$R_{\theta JA}$	52	°C/W
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	°C

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	600	700	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V$	-	-	1.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	2.9	3.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 1A$	-	785	1008	m Ω
Dynamic Characteristics⁷⁾						
Input Capacitance	C_{iss}	$V_{DS} = 100V, V_{GS} = 0V,$ $f = 1.0MHz$	-	232.7	-	pF
Output Capacitance	C_{oss}		-	11.5	-	
Reverse Transfer Capacitance	C_{rss}		-	0.8	-	
Switching Characteristics⁷⁾						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 400V, V_{GS} = 10V,$ $I_D = 1A, R_G = 10\Omega$	-	9.7	-	ns
Turn-on Rise Time	t_r		-	8.1	-	
Turn-Off Delay Time	$t_{d(off)}$		-	29.3	-	
Turn-Off Fall Time	t_f		-	34.5	-	
Total Gate Charge	Q_g	$V_{DS} = 480V, V_{GS} = 10V,$ $I_D = 1A$	-	6.4	-	nC
Gate-Source Charge	Q_{gs}		-	1.1	-	
Gate-Drain Charge	Q_{gd}		-	2.5	-	
Gate Resistance	R_g	$f=1MHz$, Open Drain	-	5.6	-	Ω
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 1A$	-	0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 1A, V_R = 200V,$ $dI_F/dt = 100A/\mu s$	-	102	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	430.7	-	μC
Peak Reverse Recovery Current	I_{rrm}		-	8.45	-	A

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature($T_{J_Max}=150^\circ C$).
3. Pulse Test: Pulse Width $\leq 10\mu s$, Duty Cycle $\leq 1\%$.
4. This single-pulse measurement was taken under the following condition [$L=20mH, V_{GS}=10V, V_{DS}=100V$]while it's value is limited by $T_{J_Max}=150^\circ C$.
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on infinite heatsink.
7. Guaranteed by design, not subject to production.

Typical Characteristics

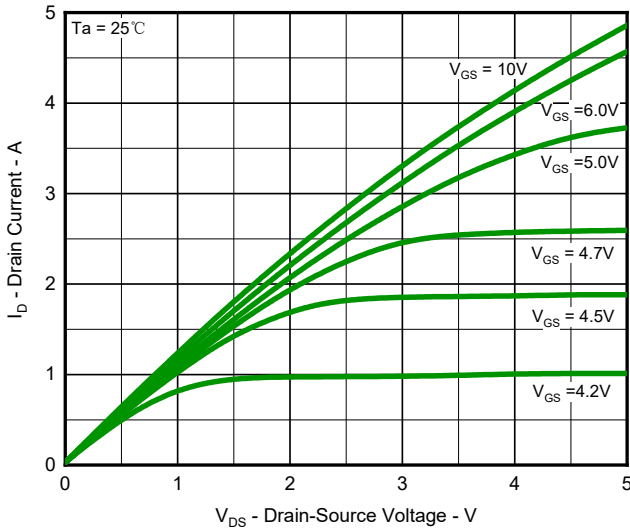


Fig.1 Output Characteristics

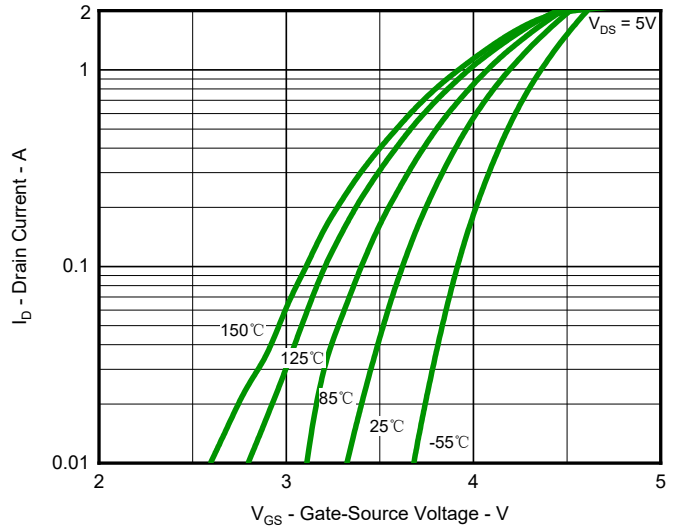


Fig.2 Typical Transfer Characteristic

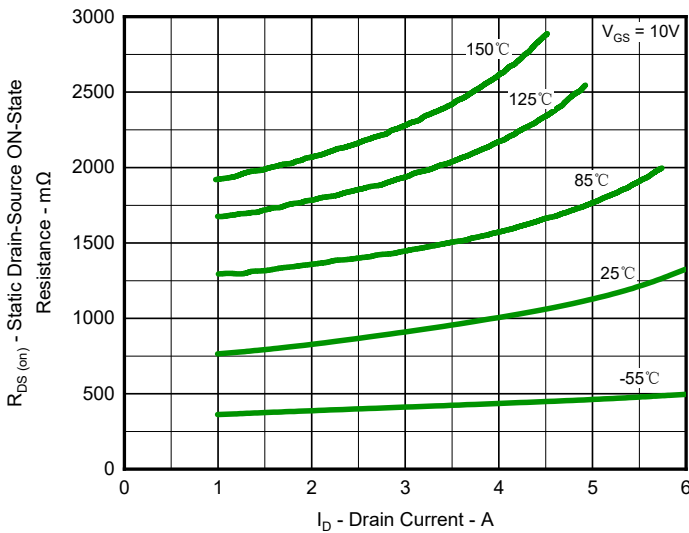


Fig.3 Typical On-Resistance vs Drain Current and Temperature

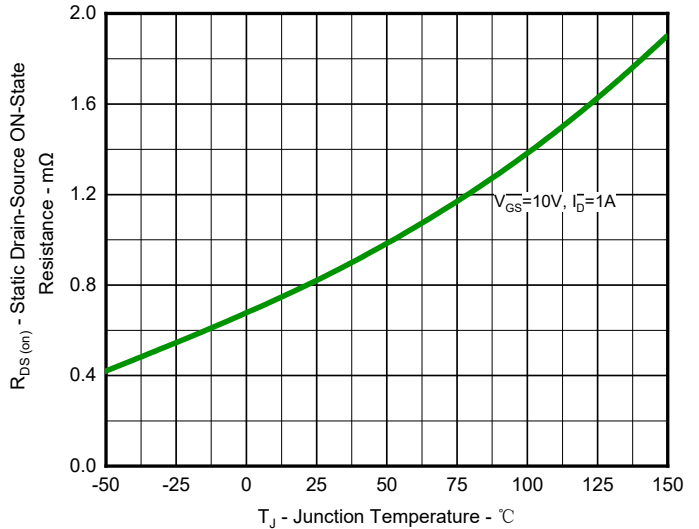


Fig.4 On-Resistance Variation with Temperature

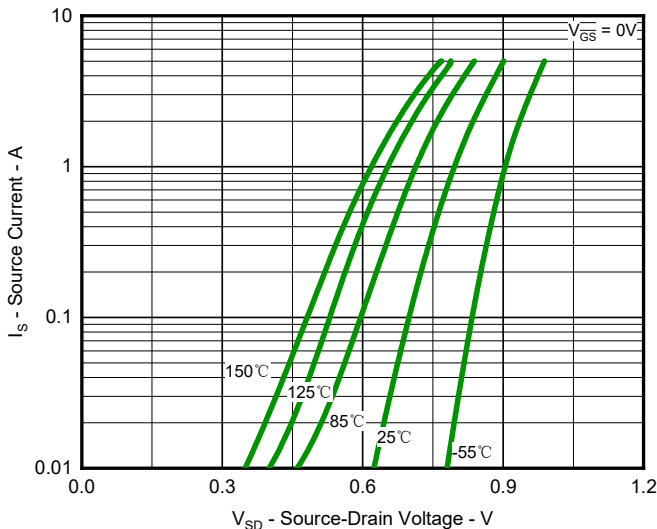


Fig.5 Diode Forward Voltage vs. Current

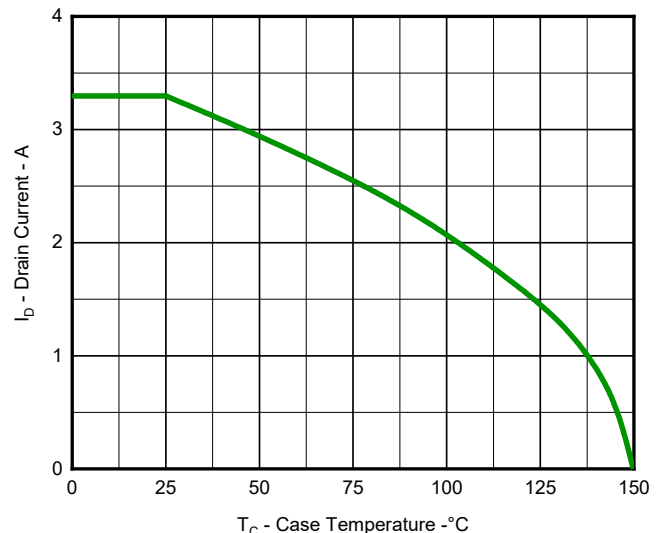


Fig.6 Maximum Drain Current vs. Case Temperature

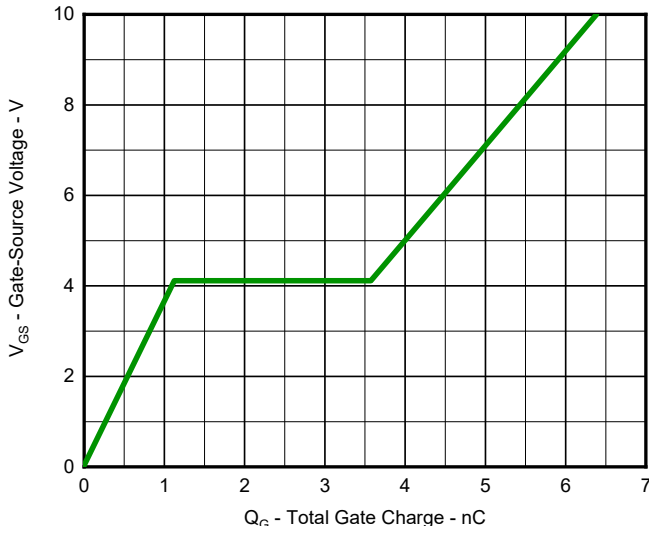


Fig.7 Gate Charge Characteristics

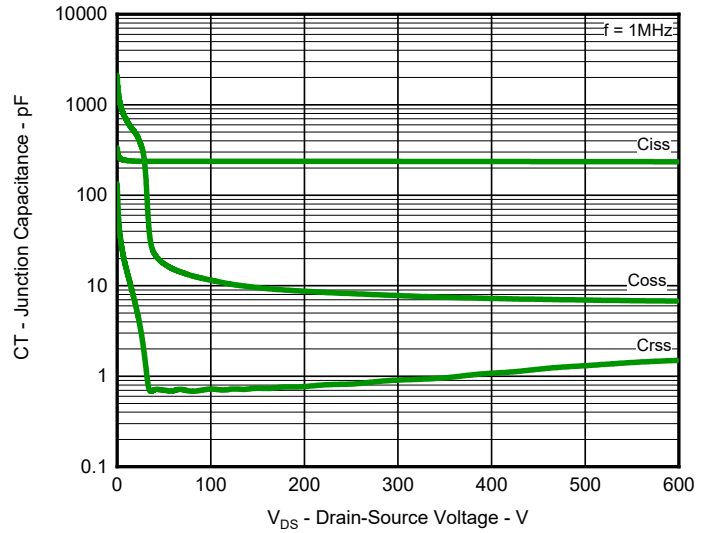


Fig.8 Typical Junction Capacitance

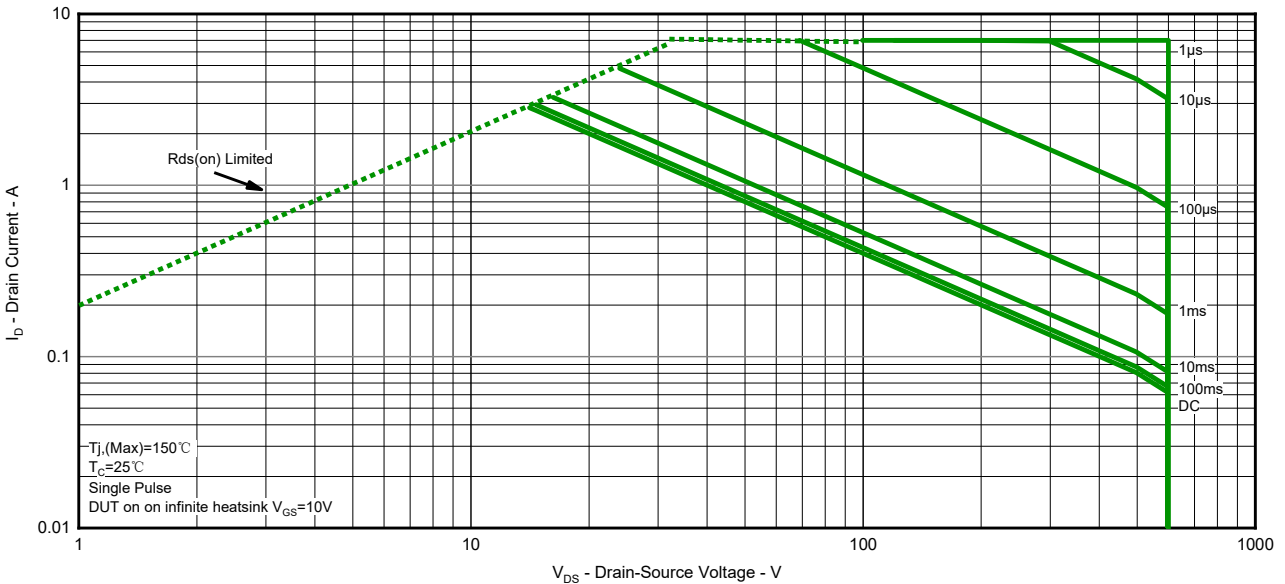


Fig.9 Safe Operation Area

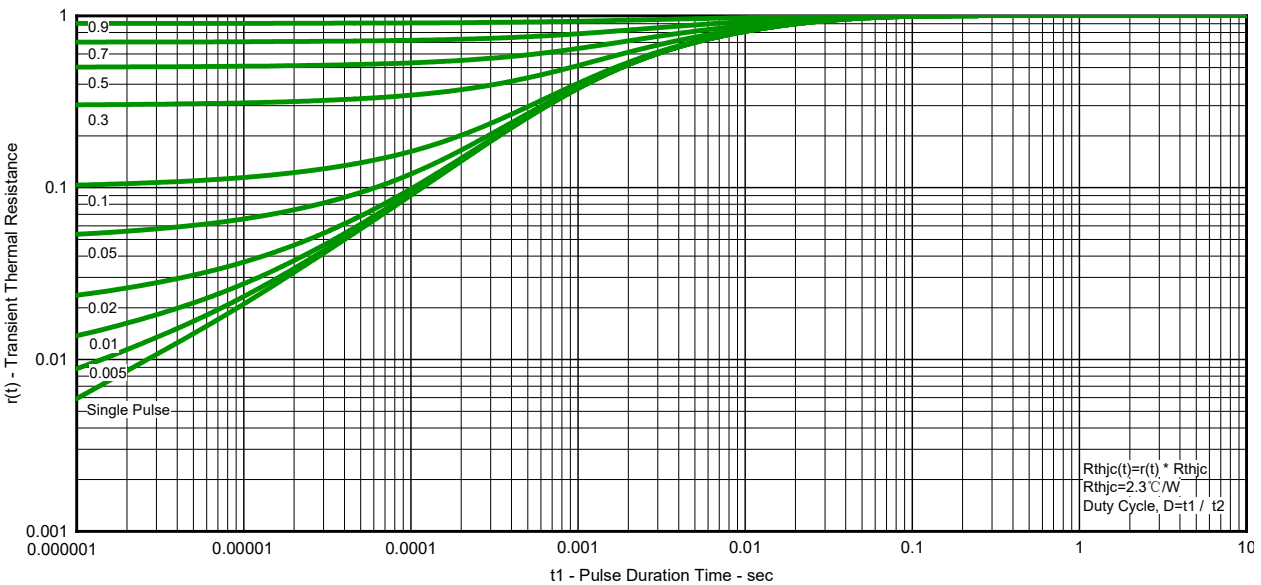
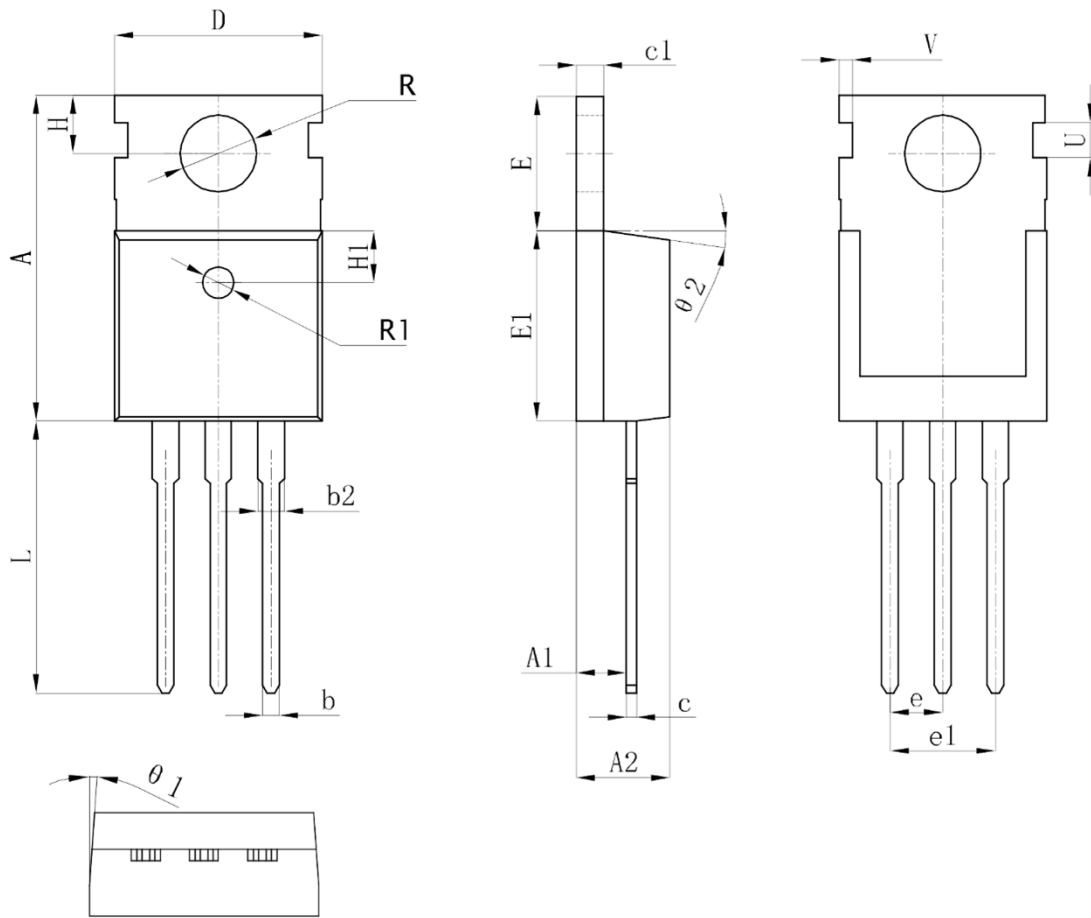



Fig.10 Transient Thermal Resistance

Product dimension (TO-220)



Dim	Millimeters		Inches		Dim	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	15.40	15.80	0.606	0.622	e1	4.84	5.32	0.191	0.209
A1	2.35	2.50	0.093	0.098	H	2.73	2.87	0.107	0.113
A2	4.40	4.70	0.173	0.185	H1	2.40	2.60	0.094	0.102
b	0.70	0.90	0.028	0.035	L	13.02	13.72	0.513	0.540
b2	1.18	1.44	0.046	0.057	R	3.50	3.63	0.138	0.143
c	0.48	0.56	0.019	0.022	R1	1.40	1.60	0.055	0.063
c1	1.29	1.32	0.051	0.052	U	1.65	1.85	0.065	0.073
D	9.80	10.20	0.386	0.402	V	0.58	0.78	0.023	0.031
E	6.40	6.60	0.252	0.260	$\theta 1$	2°	3°	2°	3°
E1	9.00	9.20	0.354	0.362	$\theta 2$	6.5°	7.5°	6.5°	7.5°
e	2.42	2.66	0.095	0.105					


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